



# TIP140/141/142 TIP145/146/147

## COMPLEMENTARY SILICON POWER DARLINGTON TRANSISTORS

- TIP141, TIP142, TIP145 AND TIP147 ARE STMicroelectronics PREFERRED SALESTYPES
- COMPLEMENTARY PNP - NPN DEVICES
- MONOLITHIC DARLINGTON CONFIGURATION
- INTEGRATED ANTIPARALLEL COLLECTOR-EMITTER DIODE

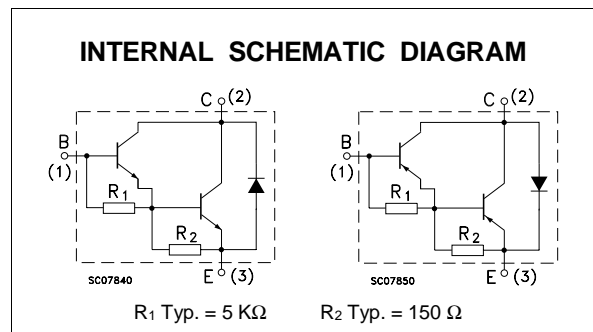
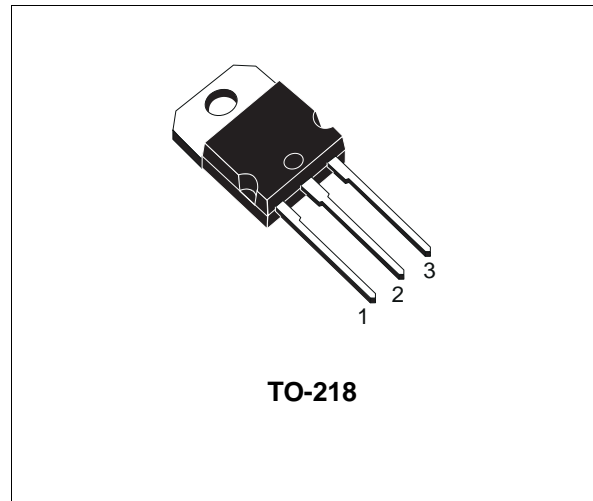
### APPLICATIONS

- LINEAR AND SWITCHING INDUSTRIAL EQUIPMENT

### DESCRIPTION

The TIP140, TIP141 and TIP142 are silicon Epitaxial-Base NPN power transistors in monolithic Darlington configuration, mounted in TO-218 plastic package. They are intended for use in power linear and switching applications.

The complementary PNP types are TIP145, TIP146 and TIP147 respectively.



### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value				Unit
		NPN	TIP140	TIP141	TIP142	
		PNP	TIP145	TIP146	TIP147	
V <sub>CBO</sub>	Collector-Base Voltage (I <sub>E</sub> = 0)		60	80	100	V
V <sub>CEO</sub>	Collector-Emitter Voltage (I <sub>B</sub> = 0)		60	80	100	V
V <sub>EBO</sub>	Emitter-Base Voltage (I <sub>C</sub> = 0)		5			V
I <sub>C</sub>	Collector Current		10			A
I <sub>CM</sub>	Collector Peak Current		20			A
I <sub>B</sub>	Base Current		0.5			A
P <sub>tot</sub>	Total Dissipation at T <sub>case</sub> ≤ 25 °C		125			W
T <sub>stg</sub>	Storage Temperature		-65 to 150			°C
T <sub>j</sub>	Max. Operating Junction Temperature		150			°C

For PNP types voltage and current values are negative.

# TIP140 / TIP141 / TIP142 / TIP145 / TIP146 / TIP147

## THERMAL DATA

R <sub>thj-case</sub>	Thermal Resistance Junction-case	Max	1	°C/W
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## ELECTRICAL CHARACTERISTICS (T<sub>case</sub> = 25 °C unless otherwise specified)

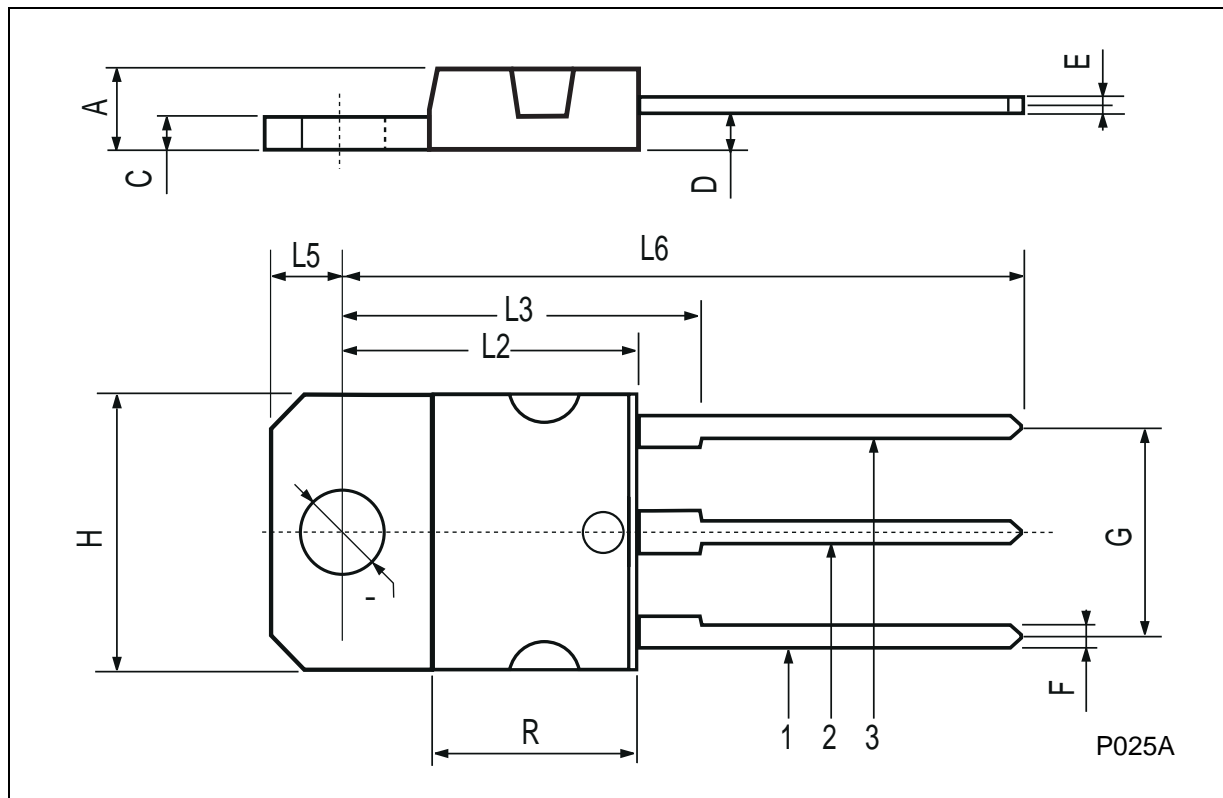
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I <sub>CBO</sub>	Collector Cut-off Current (I <sub>E</sub> = 0)	for <b>TIP140/145</b> V <sub>CB</sub> = 60 V for <b>TIP141/146</b> V <sub>CB</sub> = 80 V for <b>TIP142/147</b> V <sub>CB</sub> = 100 V			1 1 1	mA mA mA
I <sub>CEO</sub>	Collector Cut-off Current (I <sub>B</sub> = 0)	for <b>TIP140/145</b> V <sub>CE</sub> = 30 V for <b>TIP141/146</b> V <sub>CE</sub> = 40 V for <b>TIP142/147</b> V <sub>CE</sub> = 50 V			2 2 2	mA mA mA
I <sub>EBO</sub>	Emitter Cut-off Current (I <sub>C</sub> = 0)	V <sub>EB</sub> = 5 V			2	mA
V <sub>CEO(sus)</sub> *	Collector-Emitter Sustaining Voltage (I <sub>B</sub> = 0)	I <sub>C</sub> = 30 mA for <b>TIP140/145</b> for <b>TIP141/146</b> for <b>TIP142/147</b>	60 80 100			V V V
V <sub>CE(sat)</sub> *	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 5 A I <sub>B</sub> = 10 mA I <sub>C</sub> = 10 A I <sub>B</sub> = 40 mA			2 3	V V
V <sub>BE(on)</sub> *	Base-Emitter Voltage	I <sub>C</sub> = 10 A V <sub>CE</sub> = 4 V			3	V
h <sub>FE</sub> *	DC Current Gain	I <sub>C</sub> = 5 A V <sub>CE</sub> = 4 V I <sub>C</sub> = 10 A V <sub>CE</sub> = 4 V	1000 500			
t <sub>on</sub> t <sub>off</sub>	RESISTIVE LOAD Turn-on Time Turn-off Time	I <sub>C</sub> = 10 A I <sub>B1</sub> = 40 mA I <sub>B2</sub> = -40 mA R <sub>L</sub> = 3 Ω		0.9 4		μs μs

For PNP types voltage and current values are negative.

\* Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %

## TO-218 (SOT-93) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.7		4.9	0.185		0.193
C	1.17		1.37	0.046		0.054
D		2.5			0.098	
E	0.5		0.78	0.019		0.030
F	1.1		1.3	0.043		0.051
G	10.8		11.1	0.425		0.437
H	14.7		15.2	0.578		0.598
L2	–		16.2	–		0.637
L3		18			0.708	
L5	3.95		4.15	0.155		0.163
L6		31			1.220	
R	–		12.2	–		0.480
Ø	4		4.1	0.157		0.161



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